CHAPTER 13 OUTPUT STAGES AND POWER AMPLIFIERS

Chapter Outline

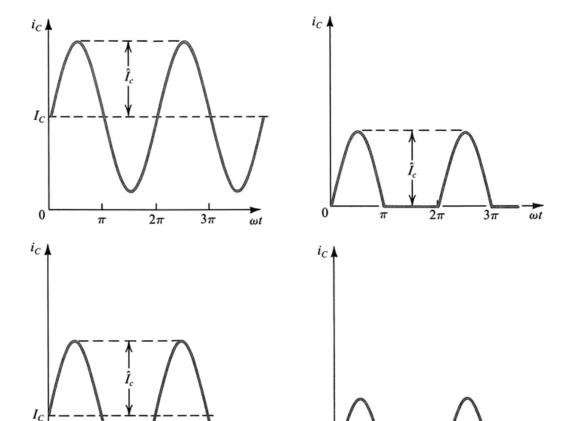
- 13.1 Classification of Output Stages
- 13.2 Class A Output Stage
- 13.3 Class B Output Stage
- 13.4 Class AB Output Stage
- 13.5 Biasing the Class AB Circuit
- 13.6 CMOS Class AB Output Stages

13.1 CLASSIFICATIONS OF OUTPUT STAGES

Output Stages □ Class A output stage: ■ Bias current is greater than the magnitude of the signal current ■ Conduction angle is 360° □ Class B output stage: ■ Biased at zero dc current ■ Conduction angle is 180° ■ Another transistor conducts during the alternate half-cycle □ Class AB output stage: ■ An intermediate class between A and B ■ Biased at a nonzero dc current much smaller than the peak current of the signal ■ Conduction angle is greater than 180° but much smaller than 360° ■ Two transistors are used and currents are combined at the load □ Class C output stage:

- Conduction angle is smaller than 180°
- The current is passed through a parallel *LC* network to obtain the output signal
- ☐ Class A, B and AB are used as output stage of op amps
- ☐ Class AB amplifiers are preferred for audio power amplifier
- ☐ Class C amplifiers are usually used at higher frequencies

- ☐ Collector current waveforms for the transistors operating in different classes
- ☐ The classification also applies for output stages with MOSFETs



ωt

 3π

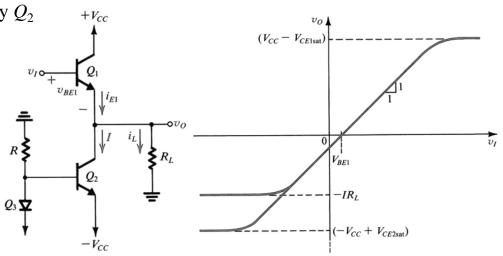
 2π

13.2 CLASS A OUTPUT STAGE

Transfer Characteristics

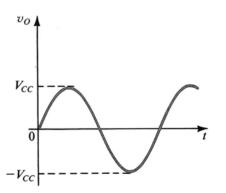
 \square Q_1 biased with a constant current I supplied by Q_2

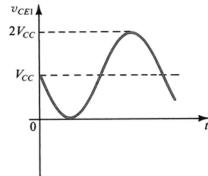
$$\begin{split} v_O &= v_I - v_{BE1} \\ v_{O\max} &= V_{CC} - V_{CE1sat} \\ v_{O\min} &= -IR_L \text{ or } v_{O\min} = -V_{CC} + V_{CE2sat} \\ I &\geq \frac{|-V_{CC} + V_{CE2sat}|}{R_L} \end{split}$$

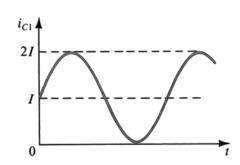


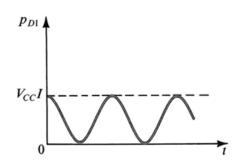
Signal Waveforms

- \Box The output swing from $-V_{\rm CC}$ to $V_{\rm CC}$ for $I = V_{\rm CC}/R_{\rm L}$
- ☐ The instantaneous power dissipation in Q_1 : $P_{D1} = v_{CE1}i_{C1}$



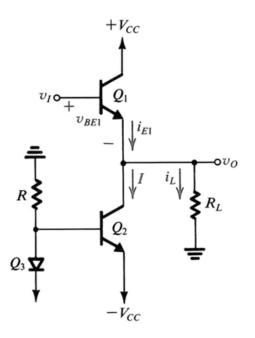






Power Dissipation

- \square Power dissipation for $R_{\rm L} = V_{CC}/I$:
 - The maximum instantaneous power dissipation in Q_1 is $V_{CC}I$
 - This is equal to the power dissipation in Q_1 with no input signal applied (quiescent power dissipation)
 - The transistor Q_1 much be able to withstand a continuous power dissipation of $V_{CC}I$
- ☐ Power dissipation for unloaded case:
 - Maximum power dissipation occurs when $v_0 = -V_{CC}$
 - The maximum power dissipation in Q_1 is $2V_{CC}I$
- ☐ Power dissipation for an output short circuit:
 - A positive input may lead to an infinite load current
 - The output stages are usually equipped with short-circuit protection to guard against such a situation
- \square Power dissipation in Q_2 :
 - \blacksquare Q_2 conducts a constant current I
 - \blacksquare Maximum voltage across the collector and the emitter is $2V_{\rm CC}$
 - Maximum instantaneous power dissipation in Q_2 is $2V_{CC}I$
 - \blacksquare A more significant quantity for design purposes is the average power dissipation of $V_{\rm CC}I$



Power Conversion Efficiency

- \square The power conversion efficiency is defined as $\eta \equiv P_L(\text{load power})/P_S(\text{supply power})$
- \square The load power (P_L) with an sinusoid output with a peak value of $\hat{V_o}$ is

$$P_{L} = \frac{(\hat{V_{o}}/\sqrt{2})^{2}}{R_{L}} = \frac{1}{2} \frac{\hat{V_{o}}^{2}}{R_{L}}$$

- \Box The total average supply power is $P_S = 2V_{CC}I$
- \Box The conversion efficiency is given by

$$\eta = \frac{1}{4} \frac{\widehat{V_o}^2}{IR_L V_{CC}} = \frac{1}{4} \left(\frac{\widehat{V_o}}{IR_L} \right) \left(\frac{\widehat{V_o}}{V_{CC}} \right)$$

- \square Maximum efficiency (25%) is obtained when $\hat{V_o} = V_{CC} = IR_L$
- ☐ Class A output stage is rarely used in high-power applications
- ☐ The efficiency achieved in practice is usually in the range of 10% to 20%

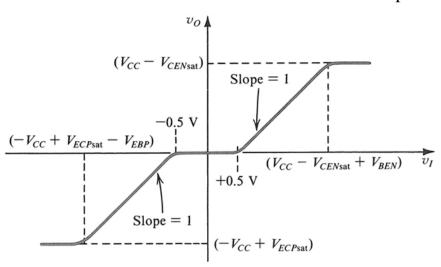
13.3 CLASS B OUTPUT STAGE

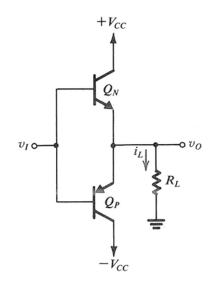
Circuit Operation

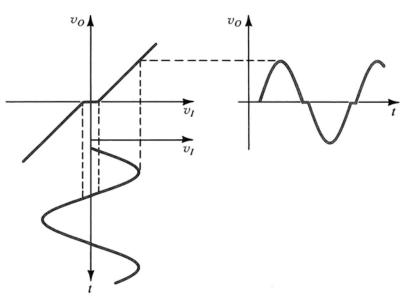
- \square Both transistors are cut off when v_I is zero $\rightarrow v_O$ is zero
- \Box One of the transistor turns on as $v_{\rm I}$ exceeds $\pm 0.5~{\rm V} \rightarrow v_{\rm O}$ follows $v_{\rm I}$
- ☐ The circuit operates in a push-pull fashion
- ☐ The class B stage is biased at zero current and conducts only when the input signal is present

Transfer Characteristic

- There exists a range of input centered around zero where both Q_N and Q_P are off
- ☐ The transfer characteristic shows a dead band which results in the crossover distortion at the output







Power Conversion Efficiency

☐ The average load power by neglecting the cross-over distortion is

$$P_L = \frac{1}{2} \frac{\widehat{V_o}^2}{R_L}$$

- \square The current drawn from each supply consists of half-sine waves of peak amplitude \hat{V}_{o}/R_{L}
- ☐ The average power drawn from each of the two power supply is

$$P_{S+} = P_{S-} = \frac{1}{\pi} \frac{\hat{V_o}}{R_I} V_{CC}$$

☐ The total supply power is

$$P_{S} = \frac{2}{\pi} \frac{\widehat{V_o}}{R_L} V_{CC}$$

☐ The efficiency is given by

$$\eta = \frac{\pi}{4} \frac{\widehat{V_o}}{V_{CC}}$$

 \square Maximum efficiency is obtained when the output swing is maximized ($\cong V_{CC}$):

$$\eta = \frac{\pi}{4} = 78.5\%$$

☐ The maximum average power available from a class B stage is

$$P_L = \frac{1}{2} \frac{\widehat{V_o}^2}{R_L}$$

Power Dissipation

- ☐ The quiescent power dissipation of the class B stage is zero (unlike class A)
- \Box The average power dissipation of the class B stage is given by $P_{\rm D} = P_{\rm S} P_{\rm L}$

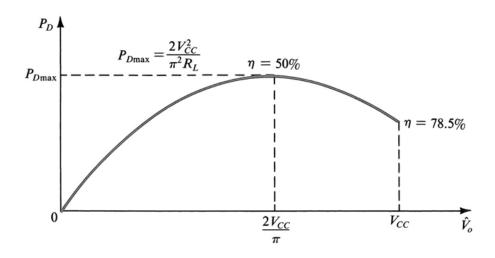
$$P_{D} = \frac{2}{\pi} \frac{\hat{V_{o}}}{R_{L}} V_{CC} - \frac{1}{2} \frac{\hat{V_{o}}^{2}}{R_{L}}$$

- \square $Q_{\rm N}$ and $Q_{\rm P}$ must be capable of safely dissipating half of $P_{\rm D}$
- \square P_{D} depends on the output swing and the worst-case power dissipation is given by

$$|\hat{V_o}|_{P_{D_{\text{max}}}} = \frac{2}{\pi} V_{CC} \rightarrow P_{D_{\text{max}}} = \frac{2}{\pi} \frac{V_{CC}^2}{R_L}$$

□ The maximum power dissipation of Q_N and Q_P occurs at $\eta = 50\%$:

$$P_{DN\,\text{max}} = P_{DP\,\text{max}} = \frac{1}{\pi} \frac{V_{CC}^2}{R_I}$$

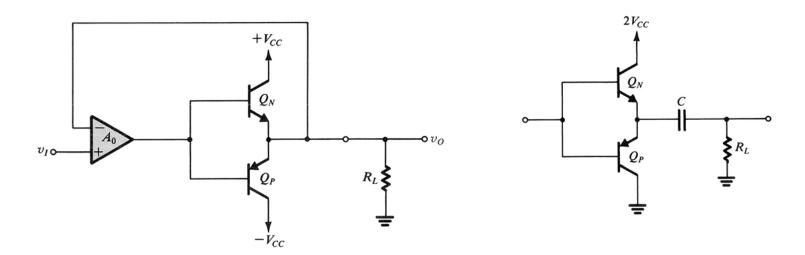


Reducing Crossover Distortion

- ☐ The distortion can be reduced by employing a high-gain op amp and overall negative feedback
- \Box The ± 0.7 V dead band is reduced by a factor of the dc gain of the op amp
- ☐ The slew rate limitation of the op amp may cause the alternate turning on and off to be noticable

Single-Supply Operation

- ☐ The class B stage can be operated from a single supply
- ☐ The load is capacitivelu coupled
- \Box The derivations are directly applicable with supply of $2V_{CC}$



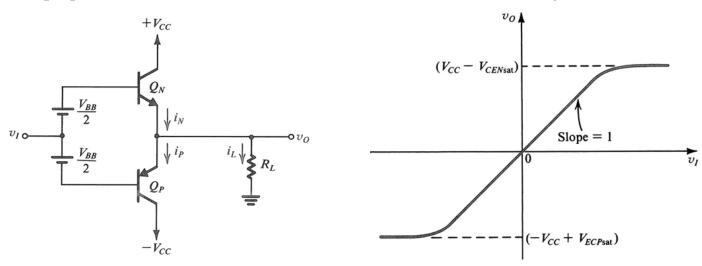
13.4 CLASS AB OUTPUT STAGE

Circuit Operation

- \square Cross-over distortion can be eliminated by biasing Q_N and Q_P at a small nonzero current
- \Box The bias current $i_{\rm N} = i_{\rm P} = I_{\rm Q} = I_{\rm s} \exp(V_{\rm BB}/2V_{\rm T})$
- \square When $v_{\rm I}$ goes positive by a certain amount:

$$\begin{split} v_{O} &= v_{I} + V_{BB} / 2 - v_{BEN} \\ v_{BEN} &+ v_{BEP} = V_{BB} \\ V_{T} &\ln \frac{i_{N}}{I_{S}} + V_{T} \ln \frac{i_{P}}{I_{S}} = 2V_{T} \ln \frac{I_{Q}}{I_{S}} \rightarrow i_{N} i_{P} = I_{Q}^{2} \rightarrow i_{N}^{2} - i_{N} i_{L} - I_{Q}^{2} = 0 \end{split}$$

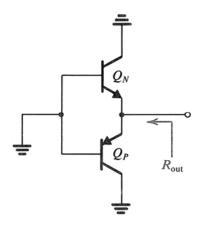
- lacktriangle The load current is supplied by $Q_{\rm N}$ which acts as the output emitter follower
- \blacksquare $Q_{\rm P}$ will be conducting a current that decreases as $v_{\rm O}$ increases (negligible for large $v_{\rm O}$)
- \square Q_P acts as the output emitter follower when v_I goes negative
- ☐ The power properties are almost identical to those derived for the class B stage



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Output Resistance

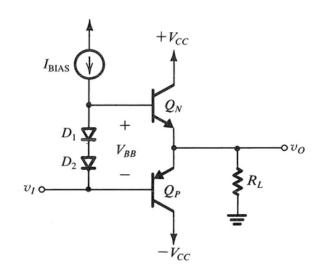
- The output resistance is estimated by assuming the source supply $v_{\rm I}$ ideal $R_{out} = r_{eN} || r_{eP} = \frac{V_T}{i_N} || \frac{V_T}{i_P} = \frac{V_T}{i_N + i_P}$
- \Box The output resistance remains approximately constant in the region around $v_I = 0$
- ☐ The output resistance decreases at larger load currents



13.5 BIASING THE CLASS AB CIRCUIT

Biasing Using Diodes

- \square The bias voltage V_{BB} is generated by passing a constant current I_{BIAS} through a pair of diodes
- ☐ The diodes need not to be large devices
- Quiescent current I_Q in Q_N and Q_P will be $I_Q = nI_{BIAS}$ where n is the ratio of the areas of the emitter junction of the BJT and the junction area of the diodes
- \square $I_{\rm BN}$ increases from $I_{\rm Q}/\beta_{\rm N}$ to $I_{\rm L}/\beta_{\rm N}$ for a positive $v_{\rm O}$
- \square I_{BIAS} has to be greater than the I_{BN} for maximum I_{L} case
- \Box The ratio n cannot be a large number as $n = I_Q/I_{BIAS}$
- ☐ This biasing arrangement provides thermal stabilization of the quiescent current in the output stage
 - \blacksquare Collect current increases with temperature for a fixed $V_{\rm BE}$
 - Heat from power dissipation increases with current
 - Positive feedback may cause thermal runaway
 - $V_{\rm BB}$ decreases at the same rate of $V_{\rm BEN}$ + $V_{\rm EBP}$
 - Thermal runaway is alleviated with close thermal contact



Biasing Using the Voltage Multiplier

lacktriangle The class AB stage can be biased by V_{BE} multiplier

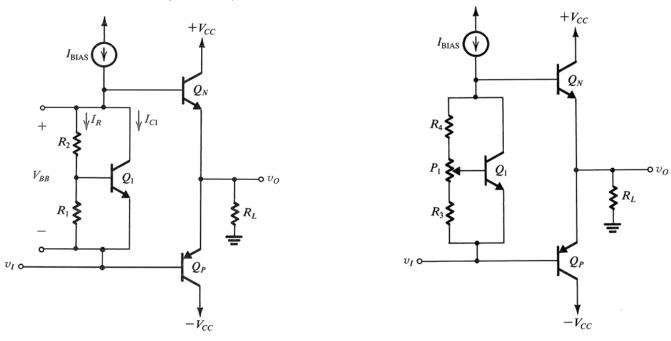
$$I_{R} = V_{BE1} / R_{1}$$

$$V_{BB} = V_{BE1} (1 + R_{2} / R_{1})$$

The value of V_{BE1} is determined by the portion of I_{BIAS} that flows through the collector of Q_1 $I_{C1} = I_{BIAS} - I_R$

$$V_{BE1} = V_T \ln \frac{I_{C1}}{I_S} = V_T \ln \frac{I_{C1}}{I_{BIAS} - I_R}$$

 \Box The quiescent current can be adjusted by the resistance value

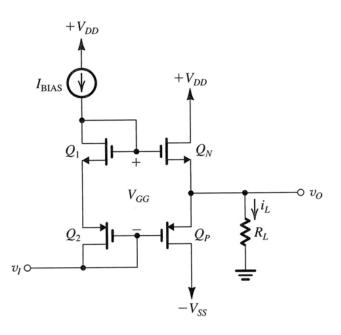


13.6 CMOS CLASS AB OUTPUT STAGES

The Classical Configuration

☐ Circuit operation

$$\begin{split} V_{GG} &= V_{GS1} + V_{SG2} = V_{th} + |V_{tp}| + \sqrt{2I_{BIAS}} \left(\frac{1}{\sqrt{k_n'(W/L)_1}} + \frac{1}{\sqrt{k_p'(W/L)_2}} \right) \\ V_{GG} &= V_{GSN} + V_{SGP} = V_{th} + |V_{tp}| + \sqrt{2I_Q} \left(\frac{1}{\sqrt{k_n'(W/L)_n}} + \frac{1}{\sqrt{k_p'(W/L)_p}} \right) \\ I_Q &= I_{BIAS} \left(\frac{1/\sqrt{k_n'(W/L)_1}}{1/\sqrt{k_n'(W/L)_n}} + \frac{1/\sqrt{k_p'(W/L)_2}}{1/\sqrt{k_p'(W/L)_p}} \right)^2 \end{split}$$



 \square For the case Q_1 and Q_2 are matched and Q_P and Q_N are matched:

$$I_Q = I_{BIAS} \frac{(W/L)_n}{(W/L)_1}$$

☐ A drawback of the CMOS class AB circuit is the restricted range of output voltage swing

$$v_{O \max} = V_{DD} - V_{OV} \mid_{BIAS} - V_{tn} - v_{OVN}$$

$$v_{O \min} = -V_{SS} + V_{OV} \mid_{I} + \mid V_{tp} \mid + \mid v_{OVP} \mid$$

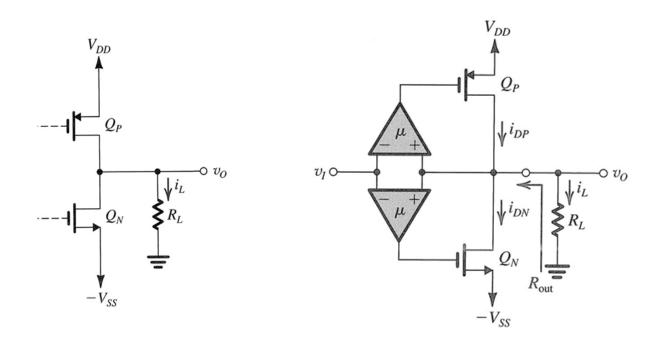
where

 $v_{
m OVN}$ is the overdrive voltage of $Q_{
m N}$ when it is supplying $i_{
m Lmax}$ and

 $|v_{\text{OVP}}|$ is the overdrive voltage of Q_{P} when sinking the maximum negative value of i_{L}

An Alternative Circuit Using Common-Source Transistors

- ☐ The allowable output range can be increased by replacing the source followers with a pair of complementary transistors in the common-source configuration
- \square Q_P supplies the load current when v_O is positive, allowing an output as high as $V_{DD} |v_{OVP}|$
- \square $Q_{\rm N}$ sinks the load current when $v_{\rm O}$ is negative, allowing an output as low as $-V_{\rm SS} + v_{\rm OVN}$
- \Box The disadvantage is its high output resistance $R_{\rm out} = r_{\rm on} || r_{\rm op}$
- ☐ Negative feedback (**error amplifiers**) is employed to reduce the output resistance

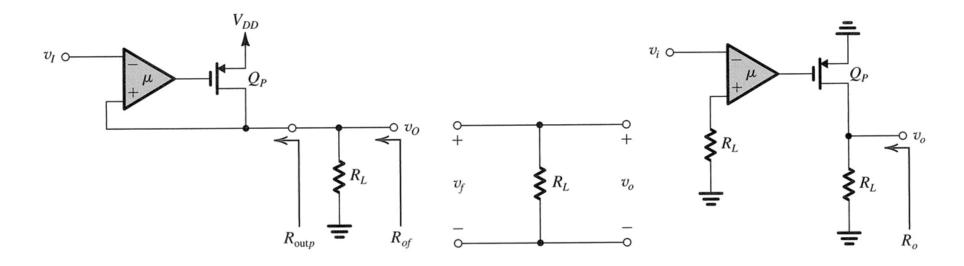


Output Resistance

- ☐ The output resistance is derived by two half circuits: $R_{out} = R_{outn} \parallel R_{outp}$
- ☐ The analysis techniques for feedback (shunt-series feedback) is utilized:

$$\beta = 1$$
 and $A = \frac{v_o}{v_i} = \mu g_{mp}(r_{op} \parallel R_L)$

- ☐ The open-loop output resistance: $R_o = R_L \parallel r_{op}$
- The output resistance with feedback: $R_{of} = R_o / (1 + \beta A) = (R_L \parallel r_{op}) / [1 + \mu g_m (R_L \parallel r_{op})]$
- The output resistance excluding R_L : $R_{outp} = 1/(1/R_{of} 1/R_L) = r_{op} \parallel \frac{1}{\mu g_{mp}} \approx \frac{1}{\mu g_{mp}}$
- Overall output resistance: $R_{out} \approx 1/\mu(g_{mp} + g_{mn})$



The Voltage Transfer Characteristics

- \square For the case where $Q_{\rm N}$ and $Q_{\rm P}$ are matched: $I_{\it Q} = \frac{1}{2}kV_{ov}^2$
- Drain currents: $i_{DN} = I_Q \left(1 + \mu \frac{v_O v_I}{V_{OV}} \right)^2$ and $i_{DP} = I_Q \left(1 \mu \frac{v_O v_I}{V_{OV}} \right)^2$
- \Box Load current: $i_L = i_{DP} i_{DN}$
- Output voltage: $v_o = v_I / \left(1 + \frac{V_{oV}}{4\mu I_Q R_L}\right) \approx v_I \left(1 \frac{V_{oV}}{4\mu I_Q R_L}\right)$
- Gain error: $v_O v_I = -\frac{V_{OV}}{4\mu I_O R_L} = -\frac{V_{OV}}{2\mu g_m R_L}$

